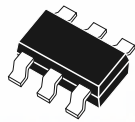


CMXSH-3
SUPER-MINI
TRIPLE ISOLATED
SURFACE MOUNT
SCHOTTKY
SWITCHING DIODE



SOT-26 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXSH-3 type contains three (3) Isolated Schottky Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a super-mini surface mount package, designed for applications requiring low forward voltage drop. Marking code is XH3.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

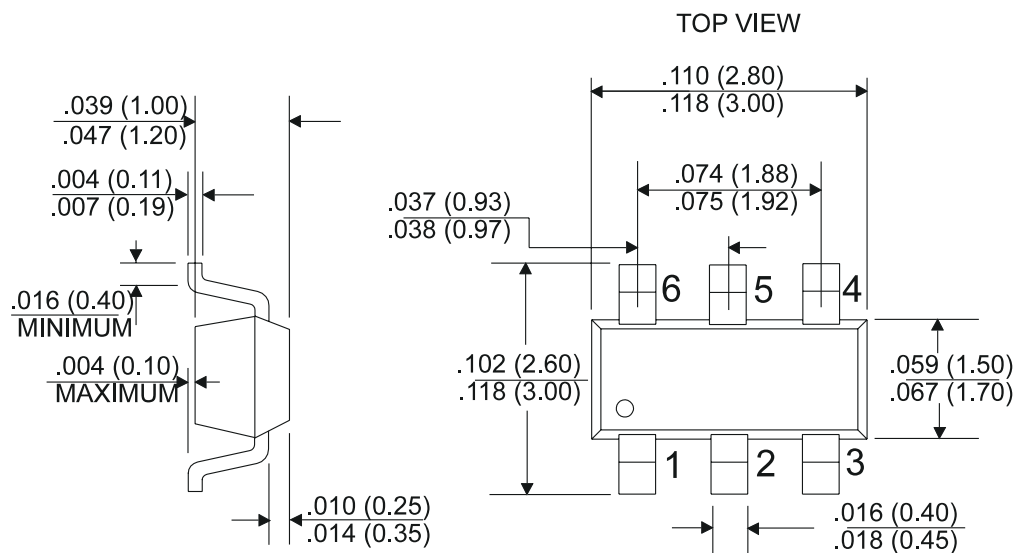
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Continuous Forward Current	I_F	100	mA
Peak Repetitive Forward Current	I_{FRM}	350	mA
Forward Surge Current, $t_p=10$ ms	I_{FSM}	750	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=25\text{V}$		90	500	nA
I_R	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	μA
BV_R	$I_R=100\mu\text{A}$	30			V
V_F	$I_F=2.0\text{mA}$		0.29	0.33	V
V_F	$I_F=15\text{mA}$		0.40	0.45	V
V_F	$I_F=100\text{mA}$		0.74	1.00	V
C_T	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

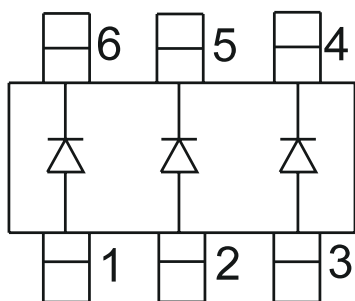
R1 (14-Sept 2000)

MECHANICAL OUTLINE - SOT-26 CASE



All Dimensions in Inches (mm)

Pin Configuration



Lead Code

- 1) Anode 1
- 2) Anode 2
- 3) Anode 3
- 4) Cathode 3
- 5) Cathode 2
- 6) Cathode 1